

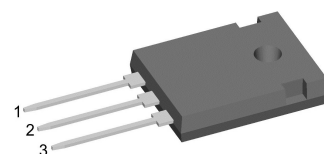
HiPerFRED²

V_{RRM}	=	200 V
I_{FAV}	= 2x	15 A
t_{rr}	=	35 ns

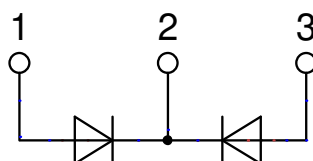
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DPG30C200HB



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

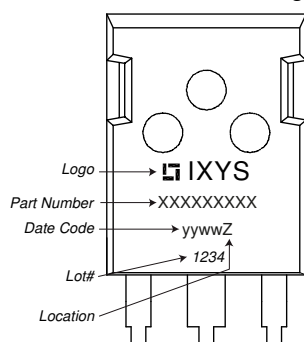
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Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				200	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				200	V	
I _R	reverse current, drain current	V _R = 200 V	T _{VJ} = 25°C			1	μA	
		V _R = 200 V	T _{VJ} = 150°C			0.08	mA	
V _F	forward voltage drop	I _F = 15 A	T _{VJ} = 25°C			1.25	V	
		I _F = 30 A				1.50	V	
		I _F = 15 A	T _{VJ} = 150°C			1.00	V	
		I _F = 30 A				1.27	V	
I _{FAV}	average forward current	T _C = 145°C rectangular d = 0.5	T _{VJ} = 175°C			15	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 175°C		0.69	V	
r _F	slope resistance					17.3	mΩ	
R _{thJC}	thermal resistance junction to case					1.7	K/W	
R _{thCH}	thermal resistance case to heatsink				0.3		K/W	
P _{tot}	total power dissipation	T _C = 25°C				90	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		240	A	
C _J	junction capacitance	V _R = 150 V f = 1 MHz		T _{VJ} = 25°C	20		pF	
I _{RM}	max. reverse recovery current	} I _F = 15 A; V _R = 130 V -di _F /dt = 200 A/μs		T _{VJ} = 25 °C	3		A	
				T _{VJ} = 125 °C	6.5		A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	35		ns	
				T _{VJ} = 125 °C	55		ns	

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part description

D = Diode
 P = HiPerFRED
 G = extreme fast
 30 = Current Rating [A]
 C = Common Cathode
 200 = Reverse Voltage [V]
 HB = TO-247AD (3)

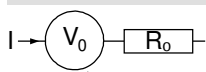
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30C200HB	DPG30C200HB	Tube	30	505797

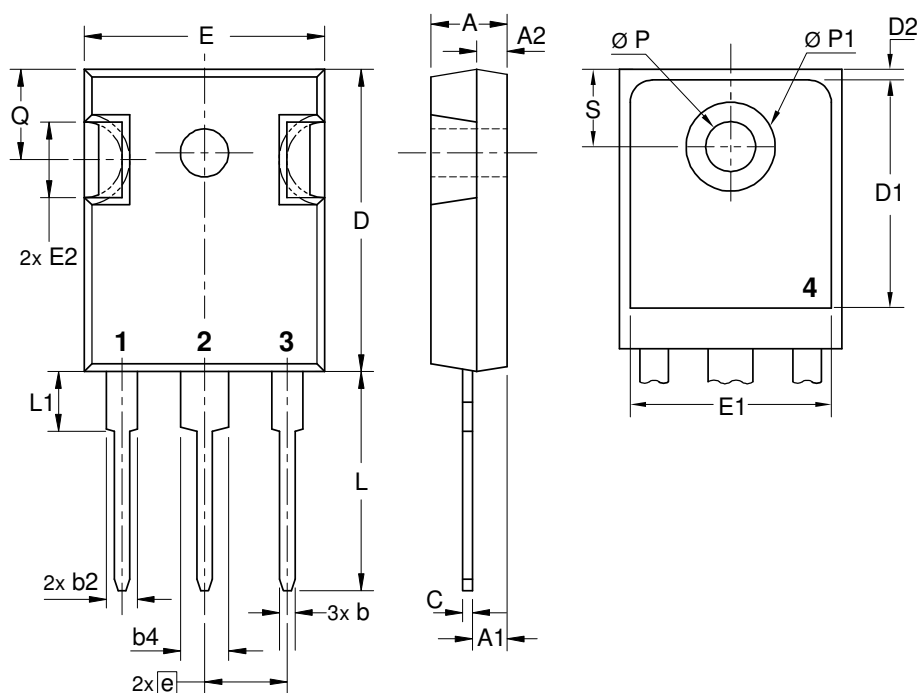
Similar Part	Package	Voltage class
DPG30C200PB	TO-220AB (3)	200
DPG30C200PC	TO-263AB (D2Pak) (2)	200

Equivalent Circuits for Simulation

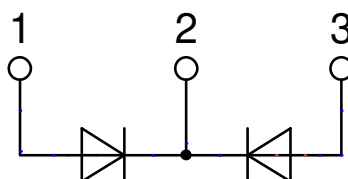
* on die level

$T_{VJ} = 175^{\circ}\text{C}$

		Fast Diode	
$V_{0\max}$	threshold voltage	0.69	V
$R_{0\max}$	slope resistance *	14.7	mΩ

Outlines TO-247


Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



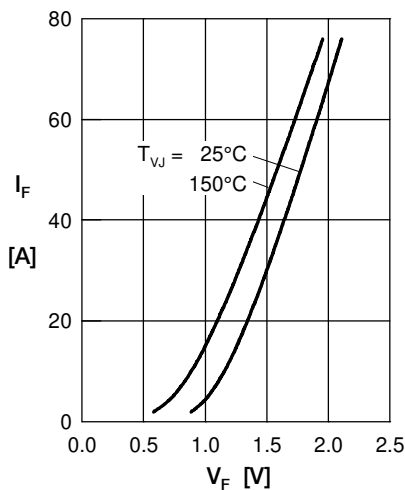
Fast Diode


Fig. 1 Forward current
 I_F versus V_F

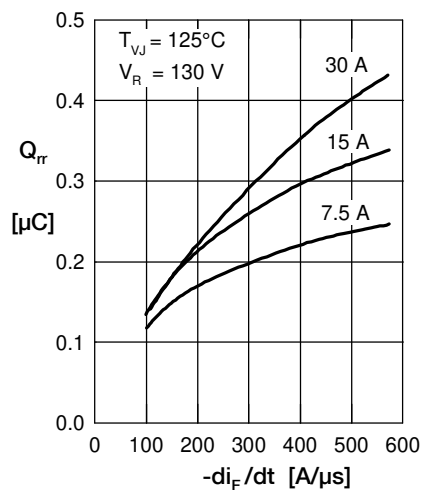


Fig. 2 Typ. reverse recov. charge
 Q_{rr} versus $-di_F/dt$

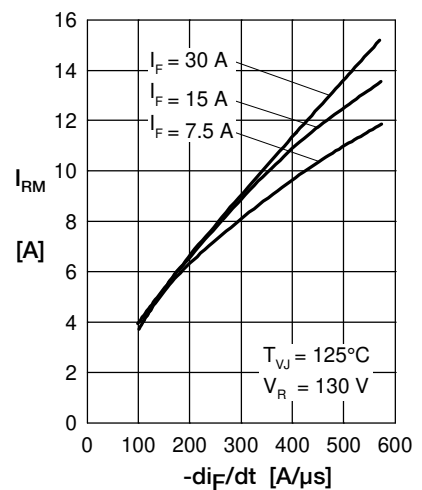


Fig. 3 Typ. peak reverse current
 I_{RM} versus $-di_F/dt$

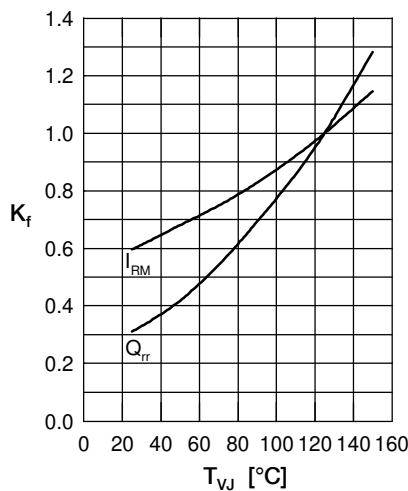


Fig. 4 Typ. dynamic parameters
 Q_{rr} , I_{RM} versus T_{VJ}

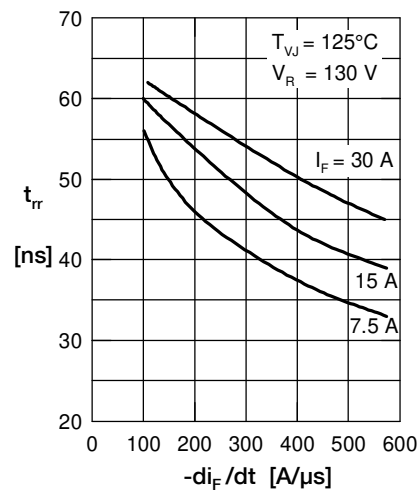


Fig. 5 Typ. recovery time
 t_{rr} versus $-di_F/dt$

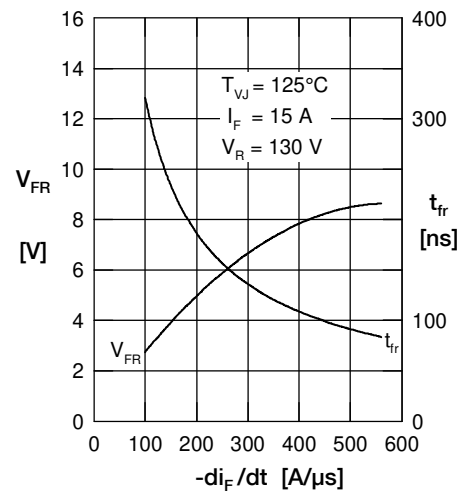


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{rr} versus di_F/dt

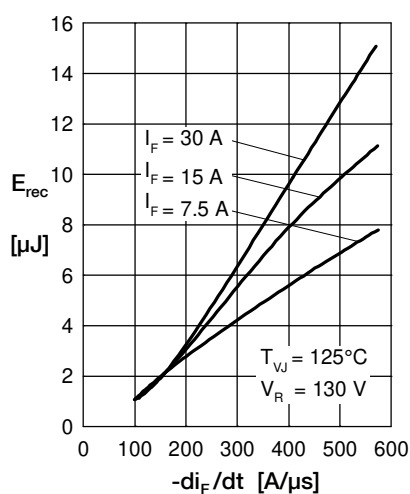


Fig. 7 Typ. recovery energy
 E_{rec} versus $-di_F/dt$

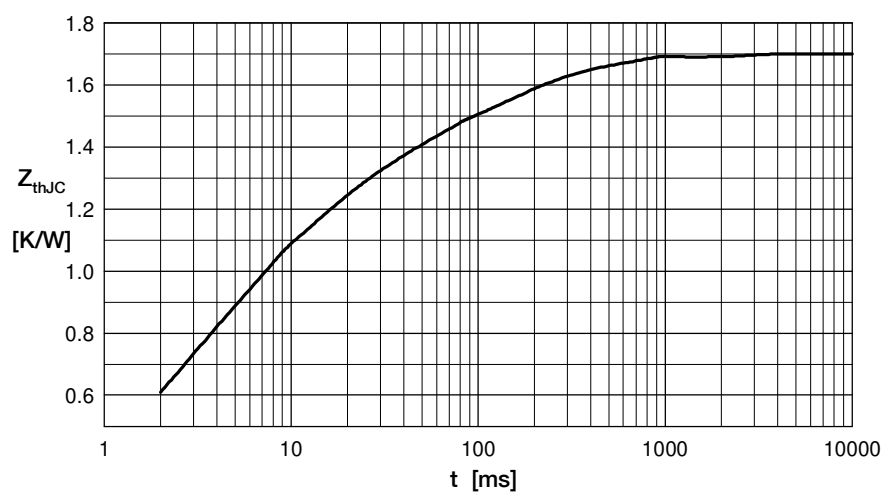


Fig. 8 Transient thermal resistance junction to case